

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO					
		Filing Date 11/19/2003		Group 2813			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/Jmm/		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
/Jmm/		US 2003/0032261 A1	2-13-2003	Yeh et al.			
/Jmm/		US 2003/0040158 A1	2-27-2003	Saitoh			
/Jmm/		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
/Jmm/		US 2004/0262784 A1	12-30-2004	Doris et al.			
/Jmm/		US 2005/0040460 A1	2-24-2005	Chidambarrao et al.			
/Jmm/		US 2005/0082634 A1	4-21-2005	Doris et al.			
/Jmm/		US 2005/0093030 A1	5-5-2005	Doris et al.			
/Jmm/		US 2005/0098829 A1	5-12-2005	Doris et al.			
/Jmm/		US 2005/0106799 A1	5-19-2005	Doris et al.			
/Jmm/		US 2005/0145954 A1	7-7-2005	Zhu et al.			
/Jmm/		US 2005/0148146 A1	7-7-2005	Doris et al.			
/Jmm/		US 2005/0194699 A1	9-8-2005	Belyansky et al.			
/Jmm/		US 2005/0236668 A1	10-27-2005	Zhu et al.			
/Jmm/		US 2005/0245017 A1	11-3-2005	Belyansky et al.			
/Jmm/		US 2005/0280051 A1	12-22-2005	Chidambarrao et al.			
/Jmm/		US 2005/0282325 A1	12-22-2005	Belyansky et al.			
/Jmm/		US 2006/0027868 A1	2-9-2006	Doris et al.			
/Jmm/		US 2006/0057787 A1	3-16-2006	Doris et al.			
/Jmm/		US 2006/0060925 A1	3-23-2006	Doris et al.			
/Jmm/		6,483,171	11-19-2002	Forbes et al.			
/Jmm/		6,831,292	12-14-2004	Currie et al.			
/Jmm/		6,717,216	4-6-2004	Doris et al.			
/Jmm/		6,825,529	11-30-2004	Chidambarrao et al.			
/Jmm/		7,015,082	3-21-2006	Doris et al.			
/Jmm/		6,974,981	12-13-2005	Chidambarrao et al.			
/Jmm/		6,977,194	12-20-2005	Belyansky et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
/Jmm/		JP 64-76755	3-22-1989	Japan			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER	/James Mitchell/		DATE CONSIDERED		03/25/2007		
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030242US1	Application No. 10/715,400		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO					
		Filing Date 11/19/2003		Group 2813			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
/Jmm/		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
/Jmm/		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." 1989 IEEE, Paper 6.2, pp. 140-143.					
/Jmm/		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991, Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
/Jmm/		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." pp. 14-15, <i>IEEE 2003, Semiconductor Device Research Symposium</i> <del>JMM</del>					
/Jmm/		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." pp. 1-5, <i>IEEE 2003, Reliability Physics Symposium Proceedings</i> <del>JMM</del>					
/Jmm/		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003, IEEE GaAs Digest, pp. 263-66.					
/Jmm/		H. Wurzer, et al., "Annealing of Degraded non-Transistors-Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.					
/Jmm/		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40					
/Jmm/		H.S. Momose, et al. "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.					
/Jmm/		M. Khater, et al., "SiGe HBT Technology with Fmax/Ft = 350/300 GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.					
/Jmm/		J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.					
/Jmm/		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.					
/Jmm/		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.					
/Jmm/		Subramanian S. Iyer, et al. " Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064					
/Jmm/		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050					
/Jmm/		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462					
/Jmm/		Q. Quyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000, IEEE, pp. 151-154.					
EXAMINER		/James Mitchell/		DATE CONSIDERED		03/25/2007	
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							